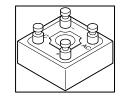


TECHNICAL DATA DATA SHEET 2014, REV. B



THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY

DESCRIPTION: A 200/400/600 VOLT, 7.5 AMP, 180 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^{\circ}$ C unless otherwise specified.

MAX. NATINGS / LLLCTRICAL C	railings are at	1A - 20 0 u	THESS OTHER W	noc opcomed.	
RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) S10A20FR S10A40FR S10A60FR	-	-	•	200 400 600	Vdc
Average DC Output Current (T _C = Case Temp) (I _o)	$T_{C} = 55 ^{\circ}\text{C}$ $T_{C} = 100 ^{\circ}\text{C}$ $T_{C} = 125 ^{\circ}\text{C}$	-	1	10 7.5 5.0	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I _o)	$T_A = 25$ °C $T_A = 55$ °C $T_A = 100$ °C	-	1	4.0 3.0 2.0	Amps
Peak Single Cycle Surge Current (I _{FSM})	t _p = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	1	100	Amps(pk)
Peak Recurring Surge Current (I _{FRM})	T _A = 25 °C	-	-	50	Amps
Operating and Storage Temp. (Top & Tstg)	-	-55	1	+150	°C
Maximum Forward Voltage (V _f)	I_f = 9.0A (300 µsec pulse, duty cycle < 2%)	-	-	1.6	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	T _A = 25° C T _A = 100° C	-	-	2.0 100	μAmps
Reverse Recovery Time (t _{rr})	I _f = 0.5A, I _r = 1.0A, I _{rr} = 0.25A	-	-	180	nsec
Thermal Resistance (θ _{JL})	-	-	-	2.0	°C/W

[•] World Wide Web - http://www.sensitron.com • E-Mail Address - sales@sensitron.com •

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MECHANICAL DIMENSIONS: In Inches / mm

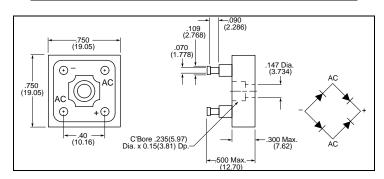


FIG. 401

Note: Case finish - Black Anodized

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